## NSN 5962-01-108-4110

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-108-4110
Body Length:
Between 0.750 inches and 0.795 inches
Body Width:
Between 0.245 inches and 0.300 inches
Body Height:
Between 0.120 inches and 0.195 inches
Maximum Power Dissipation Rating:
512.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and programmable and programmed and bipolar and 3-state output
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
Mo-001-ag joint electron device engineering council
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
35.00 nanoseconds propagation delay time, low to high level output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
13499-351-7769 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a

**Unit Of Measure:** 

## NSN 5962-01-108-4110

Memory Microcircuit - Page 2 of 2



Demilitarization:

Yes - demil/mli

Fiig:

A458a0